

# NSS30070MR6T1G

## 30 V, 0.7 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e<sup>2</sup>PowerEdge family of low  $V_{CE(sat)}$  transistors are miniature surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

### Features

- This Device is Pb-Free and is RoHS Compliant

### MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	30	V
Collector-Base Voltage	$V_{CBO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Collector Current	$I_C$	700	mA
Base Current	$I_B$	350	mA
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	$P_D$	342	mW
Total Power Dissipation @ $T_C = 85^\circ\text{C}$	$P_D$	178	mW
Thermal Resistance - Junction-to-Ambient (Note 1)	$R_{\theta JA}$	366	$^\circ\text{C}/\text{W}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	$P_D$	665	mW
Total Power Dissipation @ $T_C = 85^\circ\text{C}$	$P_D$	346	mW
Thermal Resistance - Junction-to-Ambient (Note 2)	$R_{\theta JA}$	188	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

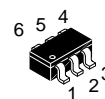
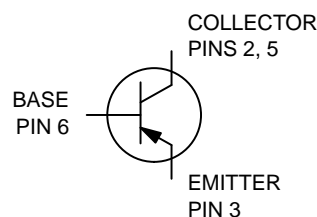
1. Minimum FR-4 or G-10 PCB, Operating to Steady State.
2. Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided), Operating to Steady State.



ON Semiconductor®

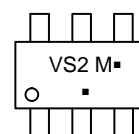
<http://onsemi.com>

**30 VOLTS**  
**0.7 AMPS**  
**PNP LOW  $V_{CE(sat)}$  TRANSISTOR**  
**EQUIVALENT  $R_{DS(on)}$  320 mΩ**



**SC-74**  
**CASE 318F**  
**STYLE 2**

### DEVICE MARKING



VS2 = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NSS30070MR6T1G	SC-74 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NSS30070MR6T1G

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-Base Breakdown Voltage (I <sub>C</sub> = 100 μA)	V <sub>(BR)CBO</sub>	40	-	-	V
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA)	V <sub>(BR)CEO</sub>	30	-	-	V
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 100 μA)	V <sub>(BR)EBO</sub>	5.0	-	-	V
Collector Cutoff Current (V <sub>CB</sub> = 25 V, I <sub>E</sub> = 0 A) (V <sub>CB</sub> = 25 V, I <sub>E</sub> = 0 A, T <sub>A</sub> = 125°C)	I <sub>CBO</sub>	-	-	1.0 10	μA
Emitter Cutoff Current (V <sub>EB</sub> = 5.0 V, I <sub>C</sub> = 0 A)	I <sub>EBO</sub>	-	-	10	μA

### ON CHARACTERISTICS

DC Current Gain (V <sub>CE</sub> = 3.0 V, I <sub>C</sub> = 100 mA)	h <sub>FE</sub>	150	-	-	V
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 500 mA, I <sub>B</sub> = 50 mA)	V <sub>CE(sat)</sub>	-	-	0.25	V
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 700 mA, I <sub>B</sub> = 70 mA)	V <sub>CE(sat)</sub>	-	-	0.4	V
Base-Emitter Saturation Voltage (I <sub>C</sub> = 700 mA, I <sub>B</sub> = 70 mA)	V <sub>BE(sat)</sub>	-	-	1.1	V
Base-Emitter Turn-On Voltage (I <sub>C</sub> = 700 mA, V <sub>CE</sub> = 1.0 V)	V <sub>BE(on)</sub>	-	-	1.0	V

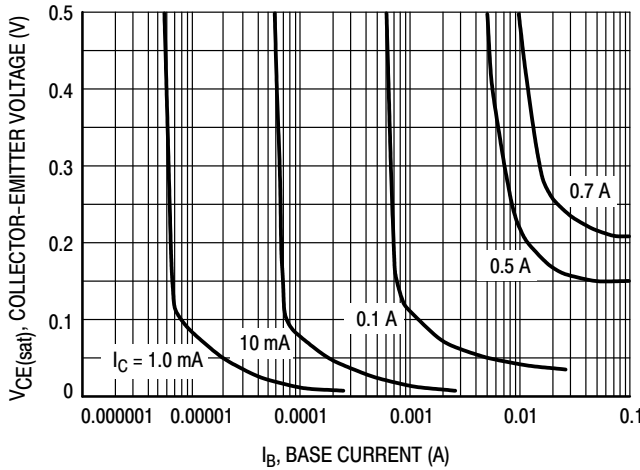


Figure 1. Collector Saturation Region

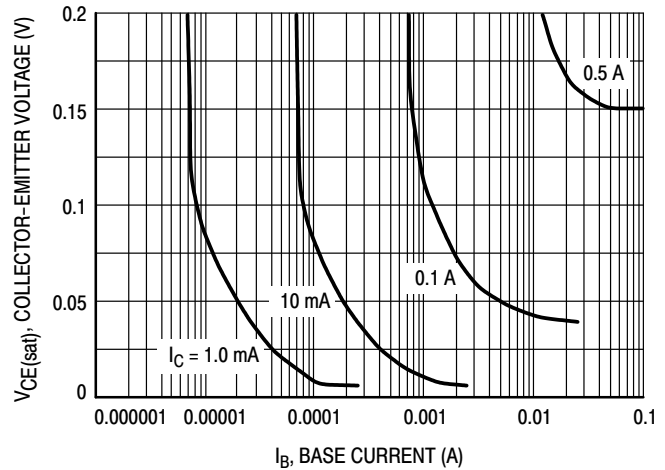


Figure 2. Collector Saturation Region

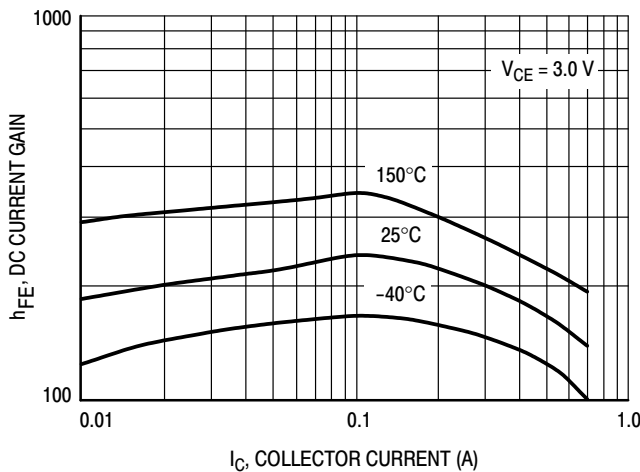


Figure 3. DC Current Gain

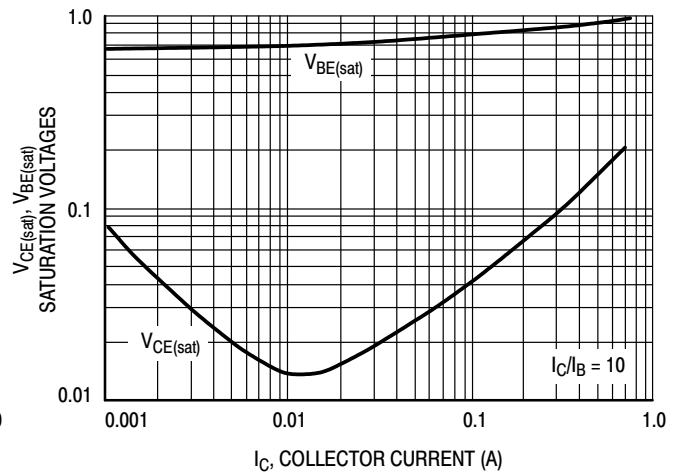


Figure 4. "SAT" Voltages

# NSS30070MR6T1G

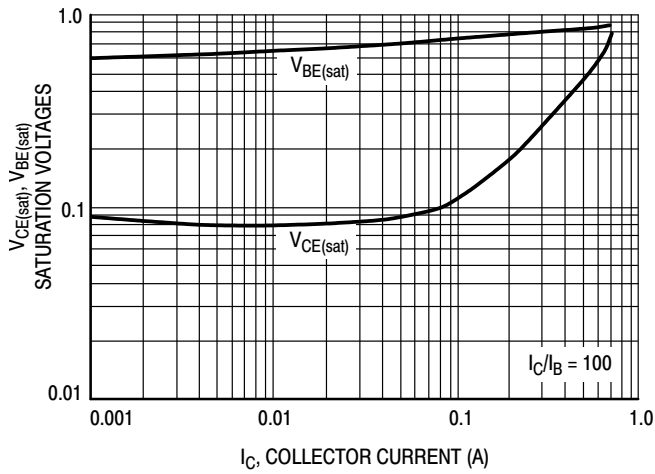


Figure 5. "SAT" Voltages

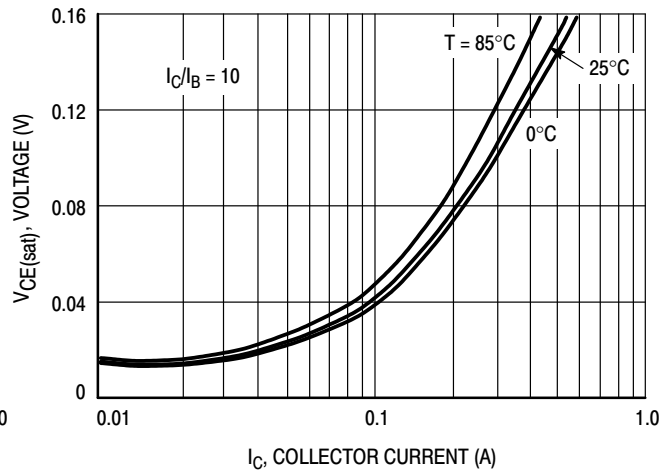


Figure 6. Collector-Emitter Saturation Voltage

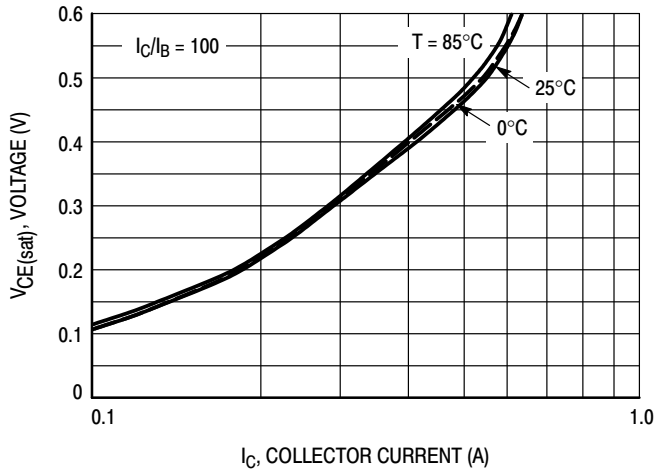


Figure 7. Collector-Emitter Saturation Voltage

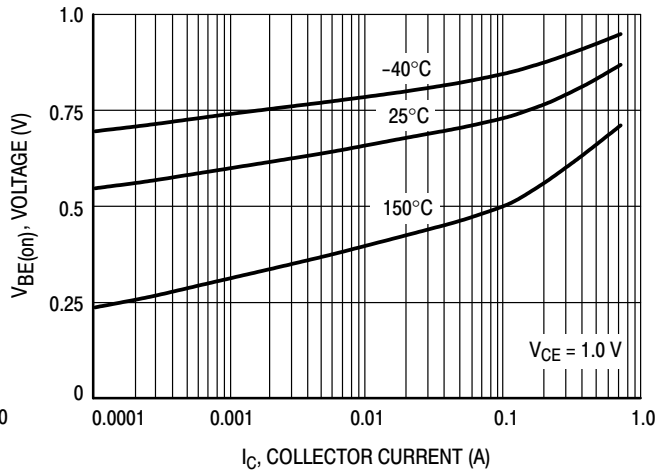


Figure 8.  $V_{BE(on)}$  Voltage

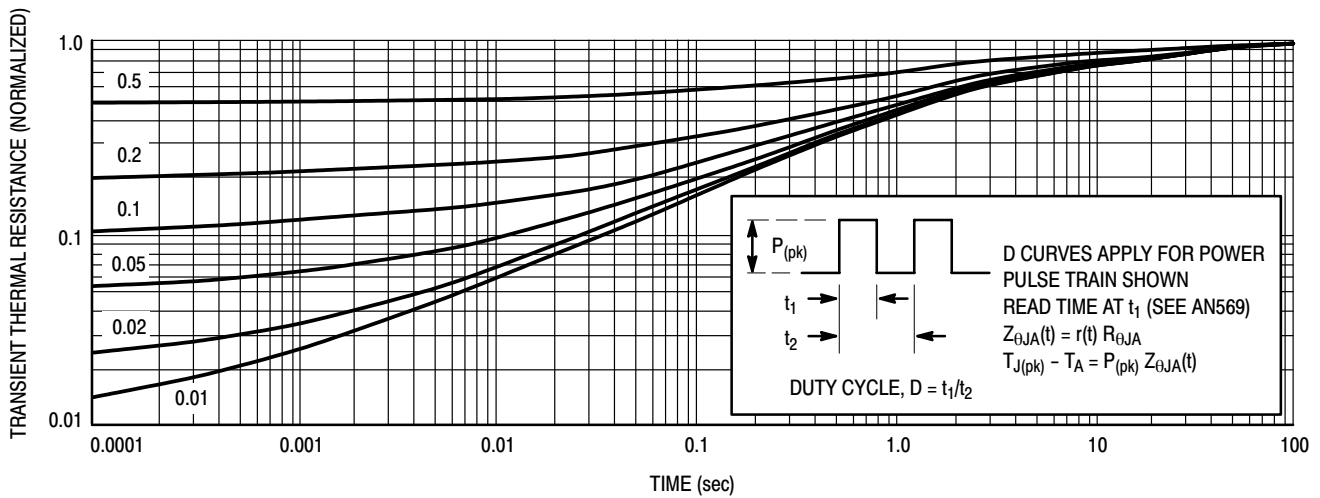


Figure 9. Thermal Response Curve

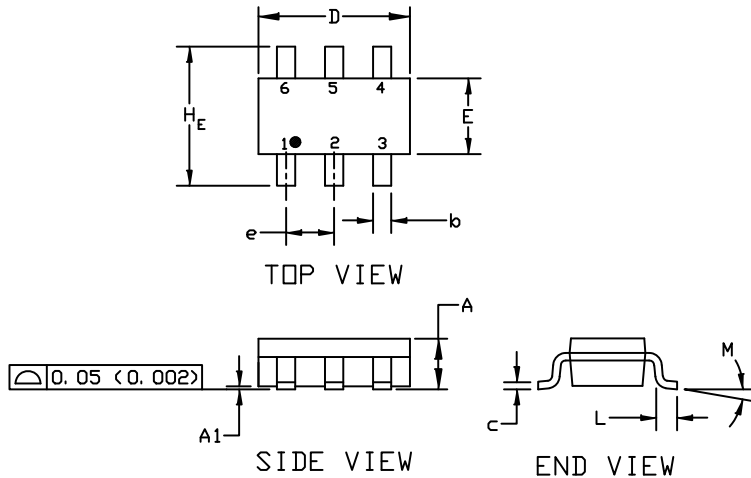
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 2:1

**SC-74**  
CASE 318F  
ISSUE P

DATE 07 OCT 2021

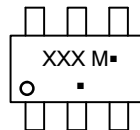


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: INCHES
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
H <sub>E</sub>	2.50	2.75	3.00	0.099	0.108	0.118
L	0.20	0.40	0.60	0.008	0.016	0.024
M	0°	---	10°	0°	---	10°

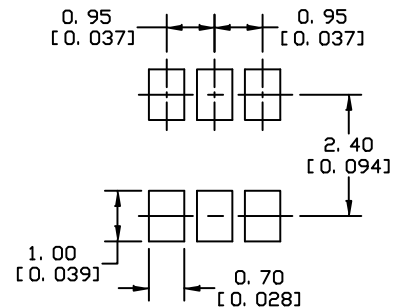
**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

**SOLDERING FOOTPRINT**

- |  |   |  |   |  |  |
|--|---|--|---|--|--|
| <p><b>STYLE 1:</b><br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. ANODE<br/>6. CATHODE</p>     | <p><b>STYLE 2:</b><br/>PIN 1. NO CONNECTION<br/>2. COLLECTOR<br/>3. EMITTER<br/>4. NO CONNECTION<br/>5. COLLECTOR<br/>6. BASE</p> | <p><b>STYLE 3:</b><br/>PIN 1. EMITTER 1<br/>2. BASE 1<br/>3. COLLECTOR 2<br/>4. EMITTER 2<br/>5. BASE 2<br/>6. COLLECTOR 1</p> | <p><b>STYLE 4:</b><br/>PIN 1. COLLECTOR 2<br/>2. EMITTER 1/EMITTER 2<br/>3. COLLECTOR 1<br/>4. EMITTER 3<br/>5. BASE 1/BASE 2/COLLECTOR 3<br/>6. BASE 3</p> | <p><b>STYLE 5:</b><br/>PIN 1. CHANNEL 1<br/>2. ANODE<br/>3. CHANNEL 2<br/>4. CHANNEL 3<br/>5. CATHODE<br/>6. CHANNEL 4</p> | <p><b>STYLE 6:</b><br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. CATHODE<br/>6. CATHODE</p> |
| <p><b>STYLE 7:</b><br/>PIN 1. SOURCE 1<br/>2. GATE 1<br/>3. DRAIN 2<br/>4. SOURCE 2<br/>5. GATE 2<br/>6. DRAIN 1</p> | <p><b>STYLE 8:</b><br/>PIN 1. EMITTER 1<br/>2. BASE 2<br/>3. COLLECTOR 2<br/>4. EMITTER 2<br/>5. BASE 1<br/>6. COLLECTOR 1</p>    | <p><b>STYLE 9:</b><br/>PIN 1. EMITTER 2<br/>2. BASE 2<br/>3. COLLECTOR 1<br/>4. EMITTER 1<br/>5. BASE 1<br/>6. COLLECTOR 2</p> | <p><b>STYLE 10:</b><br/>PIN 1. ANODE/CATHODE<br/>2. BASE<br/>3. EMITTER<br/>4. COLLECTOR<br/>5. ANODE<br/>6. CATHODE</p>                                    | <p><b>STYLE 11:</b><br/>PIN 1. EMITTER<br/>2. BASE<br/>3. ANODE/CATHODE<br/>4. ANODE<br/>5. CATHODE<br/>6. COLLECTOR</p>   |  |

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<b>DESCRIPTION:</b>	<b>SC-74</b>	<b>PAGE 1 OF 1</b>

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